Ordering number : ENN6517

Silicon Epitaxial Planar Type

DCD010

Diodes

Features

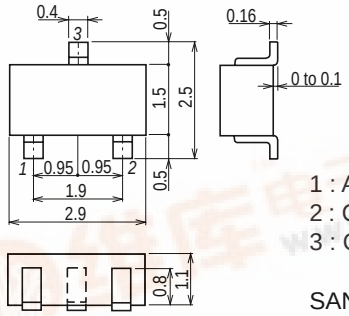
- Rectifier applications.
- Ideally suited for use in hybrid ICs because of very small-sized package.
- Small interterminal capacitance.

Package Dimensions

unit : mm

1251A

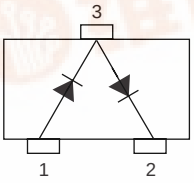
[DCD010]



1 : Anode
2 : Cathode
3 : Cathode / Anode

SANYO : CP

Electrical Connection



1 : Anode
2 : Cathode
3 : Cathode / Anode

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Peak Reverse Voltage	V_{RM}		20	V
Reverse Voltage	V_R		20	V
Peak Forward Current	I_{FM}		200	mA
Average Rectified Current	I_O		100	mA
Surge Current	I_{FSM}	(1μs)	300	mA
Allowable Power Dissipation	P		200	mW
Junction Temperature	Tj		125	°C
Storage Temperature	Tstg		-55 to +125	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Forward Voltage	V_F	I_F=10mA			1.0	V
Reverse Current	I_{R1}	V_R=15V			0.1	μA
Interterminal Capacitance	C	V_R=6V, f=1MHz			4.0	pF

Note) V_F and I_R are values per element.
C is the value for two elements.

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